Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

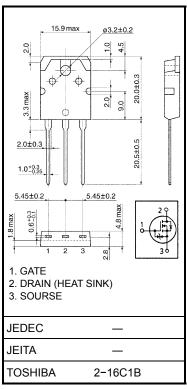
2SK2744

Chopper Regulator, DC-DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance: $RDS(ON) = 15 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: $|Y_{fs}| = 27 S$ (typ.)
- Low leakage current: $I_{DSS} = 100 \,\mu\text{A} \,(\text{max}) \,(V_{DS} = 50 \,\text{V})$
- Enhancement mode: $V_{th} = 1.5 \sim 3.5 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	50	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	50	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	45	А	
	Pulse (Note 1)	I _{DP}	180		
Drain power dissipation	n (Tc = 25°C)	P_{D}	125	W	
Single pulse avalanche energy (Note 2)		E _{AS}	95	mJ	
Avalanche current		I _{AR}	45	Α	
Repetitive avalanche e	nergy (Note 3)	E _{AR}	12.5	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature ra	ange	T _{stg}	-55~150	°C	



Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.0	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	50	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD}=25$ V, $T_{ch}=25^{\circ}C$ (initial), L=58 μH , $R_{G}=25$ Ω , $I_{AR}=45$ A

Note 3: Repetitive rating: pulse width limited by maximum junction temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.



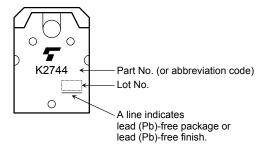
Electrical Characteristics (Ta = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current I _G		I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cut-off curre	ent	I _{DSS}	V _{DS} = 50 V, V _{GS} = 0 V	_	_	100	μА
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10$ mA, $V_{GS} = 0$ V	50	_	_	V
Gate threshold voltage		V _{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	1.5	_	3.5	V
Drain-source ON resistance		R _{DS (ON)}	V _{GS} = 10 V, I _D = 25 A	_	15	20	mΩ
Forward transfer admittance		Y _{fs}	V _{DS} = 10 V, I _D = 25 A	15	27	_	S
Input capacitance		C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	2300	_	pF
Reverse transfer capacitance		C _{rss}		_	420	_	pF
Output capacitance		Coss		_	1200	_	pF
Switching time	Rise time	t _r	$V_{GS} = 25 \text{ A} $ $V_{GS} = 25 \text{ A} $ $V_{OUT} = 25 \text{ A} $	_	30	_	
	Turn-on time	t _{on}			45	_	
	Fall time	t _f			80	_	ns
	Turn-off time	t _{off}		l	230		
Total gate charge (gate-source plus gate-drain)		Qg	10 / / / / / / / / / / / / / / / / / / /	_	68	_	nC
Gate-source charge		Qgs	$V_{DD} \simeq 40 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 45 \text{ A}$	_	20	_	nC
Gate-drain ("miller") charge		Q _{gd}		_	48	_	nC

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_		_	45	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_		_	180	Α
Forward voltage (diode)	V_{DSF}	$I_{DR} = 45 \text{ A}, V_{GS} = 0 \text{ V}$			-1.8	V
Reverse recovery time	t _{rr}	I _{DR} = 45 A, V _{GS} = 0 V		130	_	ns
Reverse recovery charge	Q _{rr}	$dI_{DR}/dt = 50 A/\mu s$	_	0.3	_	μС

Marking



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20070701-EN

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